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2N6473 2N6474 NPN
2N6475 2N6476 PNP

COMPLEMENTARY SILICON
SWITCHING TRANSISTORS

TO-220

MAXIMUM RATINGS (T_C=25°C unless otherwise noted)

	SYMBOL	2N6473 2N6475	2N6474 2N6476	UNIT
Collector-Base Voltage	V_{CBO}	110	130	V
Collector-Emitter Voltage (R_{BE}=100Ω)	V_{CER}	110	130	V
Collector-Emitter Voltage	V_{CEO}	100	120	V
Emitter-Base Voltage	V_{EBO}	5.0		V
Collector Current	I_C	4.0		A
Base Current	I_B	2.0		A
Power Dissipation	P_D	40		W
Operating and Storage Junction Temperature	T_J, Tstg	-65 TO +150		°C
Thermal Resistance	θJC	3.125		°C/W

ELECTRICAL CHARACTERISTICS (T_C=25°C unless otherwise noted)

		2N6473 2N6475		2N6474 2N6476		
SYMBOL	TEST CONDITIONS	MIN	MAX	MIN	MAX	UNIT
I_{CEV}	V_{CE}=Rated V_{CEO}, V_{BE}=1.5V		0.1		0.1	mA
I_{CEV}	V_{CE}=Rated V_{CEO}, V_{BE}=1.5V, T_C=100°C		2.0		2.0	mA
I_{CER}	V_{CE}=Rated V_{CER}, R_{BE}=100Ω		0.1		0.1	mA
I_{CER}	V_{CE}=Rated V_{CER}, R_{BE}=100Ω, T_C=100°C		2.0		2.0	mA
I_{CEO}	V_{CE}=½ Rated V_{CEO}		1.0		1.0	mA
I_{EBO}	V_{BE}=5.0V		1.0		1.0	mA
BV_{CEO}	I_C=100mA	100		120		V
BV_{CER}	I_C=100mA, R_{BE}=100Ω	110		130		V
$V_{CE(SAT)}$	I_C=1.5A, I_B=0.15A		1.2		1.2	V
$V_{CE(SAT)}$	I_C=4.0A, I_B=2.0A		2.5		2.5	V
$V_{BE(ON)}$	V_{CE}=4.0V, I_C=1.5A		2.0		2.0	V
$V_{BE(ON)}$	V_{CE}=2.5V, I_C=4.0A		3.5		3.5	V
h_{FE}	V_{CE}=4.0V, I_C=1.5A	15	150	15	150	
h_{FE}	V_{CE}=2.5V, I_C=4.0A	2.0		2.0		
h_{fe}	V_{CE}=4.0V, I_C=0.5A, f=50kHz	20		20		
f_T	V_{CE}=4.0V, I_C=0.5A (2N6473, 2N6474)	4.0		4.0		MHz
f_T	V_{CE}=4.0V, I_C=0.5A (2N6475, 2N6476)	5.0		5.0		MHz
C_{ob}	V_{CB}=10V, f=1.0MHz		250		250	pF